

the method comprising depositing a layer of semiconductor material and an exposed layer of titanium thereon on a substrate in a bridge formation, forming contact pads at opposite ends of the bridge formation, and preconditioning the titanium semiconductor bridge igniter by heating it to an elevated temperature to stabilize it against temperature-induced variations in bridge electrical resistance.

Enclosed herewith, in a separate paper, are versions of the amended paragraph of the specification and each amended claim, marked up to show the changes entered above, as required by 37 CFR 1.121 and 1.124(b).

### **REMARKS**

Claims 1 through 24 are pending in the captioned application and stand rejected under various grounds.

#### **Voluntary Amendment - Claim 1**

Claim 1 is amended to remove extraneous and potentially confusing language. As set forth in the detailed description of the invention, the bridge structure may be deposited directly upon the substrate; there is no requirement for an intervening insulation layer between them, as might be surmised from the language deleted from the claim.

#### **Voluntary Amendments to the Specification**

The amendment to the specification paragraph at page 2, lines 6-14 is entered to conform the summary of the invention to claim 1 as amended.

The amendment to the paragraph at page 2, line 31 through page 3, line 3 is entered to conform the summary of the invention to claim 12 as amended.

Support for both of the foregoing amendments can be found in the detailed description of the invention.

#### **Rejection of Claims 12-14 Under 35 USC 112**

Claim 12 and claims 13 and 14 dependent therefrom stand rejected under 35 USC 112, the Examiner asserting that it is unclear whether claim 12 is drawn to a product or a method.